

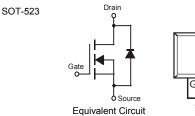
Lead-free Green 2N7002T N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

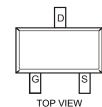
Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.002 grams (approximate)





Maximum Ratings @T_A = 25°C unless otherwise specified

Cha	racteristic	Symbol	Value	Units		
Drain-Source Voltage		V _{DSS}	60	V		
Drain-Gate Voltage R _{GS} ≤ 1.0N	ΙΩ	V _{DGR}	60	V		
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V		
Drain Current (Note 1)	Continuous Continuous @ 100°C Pulsed	ID	115 73 800	mA		

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	Pd	150	mW
Thermal Resistance, Junction to Ambient	R _{0JA}	833	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	C°

Notes: 1. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.

3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

TOP VIEW

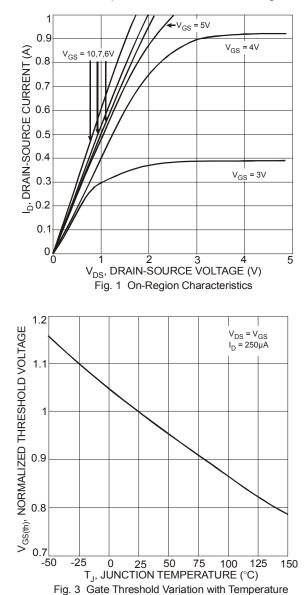
4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

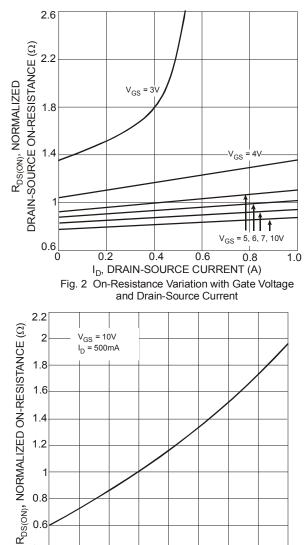


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristi	C	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)							·
Drain-Source Breakdown Voltage		BV _{DSS}	60	_	_	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}		_	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		IGSS	_		±10	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 5)		-					•
Gate Threshold Voltage		V _{GS(th)}	1.0		2.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	@ T _j = 25°C @ T _i = 125°C	R _{DS (ON)}	_	2.0 4.4	7.5 13.5	Ω	V _{GS} = 5.0V, I _D = 0.05A V _{GS} = 10V, I _D = 0.5A
On-State Drain Current		I _{D(ON)}	0.5	1.0		Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g _{FS}	80			mS	V _{DS} =10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS							•
Input Capacitance		C _{iss}	_	22	50	pF	
Output Capacitance		Coss	_	11	25	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance		C _{rss}	_	2.0	5.0	pF	
SWITCHING CHARACTERISTICS		· · ·			·		·
Turn-On Delay Time		t _{D(ON)}	_	7.0	20	ns	V _{DD} = 30V, I _D = 0.2A,
Turn-Off Delay Time		t _{D(OFF)}		11	20	ns	R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω

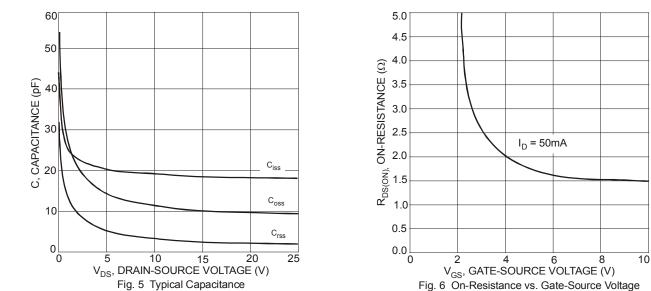
Notes: 5. Short duration pulse test used to minimize self-heating effect.





NEW PRODUCT



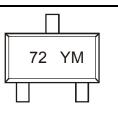


Ordering Information (Note 6)

Part Number	Case	Packaging
2N7002T-7-F	SOT-523	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

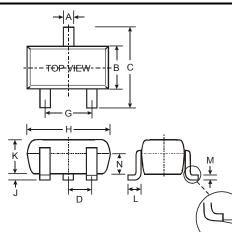
Marking Information



72 = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

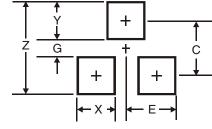
Year	2005		2006	2007		2008	2009)	20	010	2011		2012
Code	S		Т	U		V	W			Х	Y		Z
Month	Jan	Feb	Mar	Apr	May	/ Jun	Jul	Αι	ıg	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	3	9	0	Ν	D

Package Outline Dimensions



SOT-523					
Dim	Min	Max	Тур		
Α	0.15	0.30	0.22		
В	0.75	0.85	0.80		
С	1.45	1.75	1.60		
D			0.50		
G	0.90	1.10	1.00		
Н	1.50	1.70	1.60		
ر	0.00	0.10	0.05		
К	0.60	0.80	0.75		
L	0.10	0.30	0.22		
Μ	0.10	0.20	0.12		
N	0.45	0.65	0.50		
α	0°	8°	_		
All	All Dimensions in mm				





Dimensions	Value (in mm)
Z	1.9
G	0.9
Х	0.5
Y	0.5
С	1.4
Ш	0.5

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